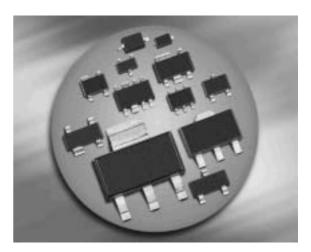


Silicon Switching Diode

- Electrically insulated high-voltage medium-speed diodes
- Pb-free (RoHS compliant) package¹⁾
- Qualified according AEC Q101





BAW101



Туре	Package	Configuration	Marking
BAW101	SOT143	parallel	JPs

Maximum Ratings at $T_A = 25^{\circ}$ C, unless otherwise specified

Parameter	Symbol	Value	Unit V
Diode reverse voltage	V _R	300	
Peak reverse voltage	V _{RM}	300	
Forward current	/ _F	250	mA
Peak forward current	/ _{FM}	500	
Peak forward current	/ _{FM}	500	mA
Surge forward current, $t = 1 \ \mu s$	I _{FS}	4.5	A
Non-repetitive peak surge forward current	I _{FSM}	-	
Total power dissipation	Ptot	350	mW
$T_{S} \leq 35^{\circ}C$			
Junction temperature	Tj	150	°C
Storage temperature	T _{stg}	-65 150	

¹Pb-containing package may be available upon special request



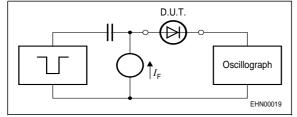
Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R _{thJS}	≤ 330	K/W
BAW101			

Electrical Characteristics at $T_A = 25^{\circ}$ C, unless otherwise specified

Parameter	Symbol	Values			Unit
			typ.	max.]
DC Characteristics					
Breakdown voltage	V _(BR)	300	-	-	V
<i>I</i> _(BR) = 100 μA					
Reverse current	I _R				μA
<i>V</i> _R = 250 V		-	-	0.15	
$V_{\rm R} = 250 \text{ V}, \ T_{\rm A} = 150 \text{ °C}$		-	-	50	
Forward voltage	V _F	-	-	1.3	V
<i>I</i> _F = 100 mA					
AC Characteristics					
Diode capacitance	CT	-	6	-	pF
$V_{\rm R} = 0 {\rm V}, f = 1 {\rm MHz}$					
Reverse recovery time	<i>t</i> _{rr}	-	1	-	μs
$I_{\rm F}$ = 10 mA, $I_{\rm R}$ = 10 mA, measured at $I_{\rm R}$ = 1mA,					
$R_{\rm L} = 100 \ \Omega$					
		ļ	I	I	

Test circuit for reverse recovery time



Pulse generator: $t_{\rm p}$ = 10µs, D = 0.05, $t_{\rm r}$ = 0.6ns, $R_{\rm i}$ = 50Ω

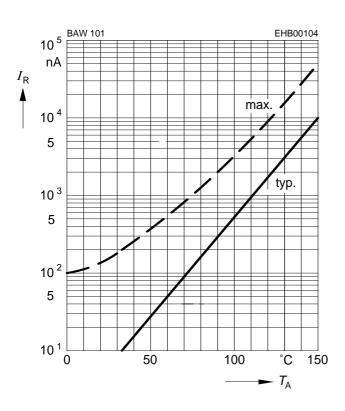
Oscillograph: $R = 50\Omega$, $t_r = 0.35$ ns, $C \le 1$ pF

¹For calculation of R_{thJA} please refer to Application Note Thermal Resistance



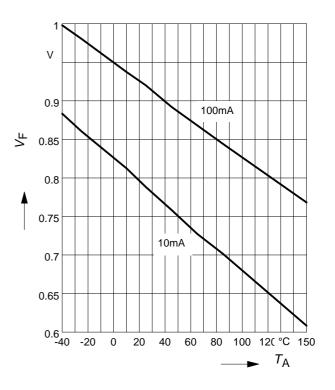
Reverse current $I_{R} = f(T_{A})$

 $V_{\rm R} = 250 \rm V$



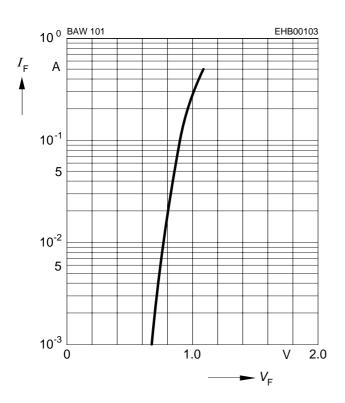
Forward Voltage $V_{\rm F} = f(T_{\rm A})$

 $I_{\rm F}$ = Parameter

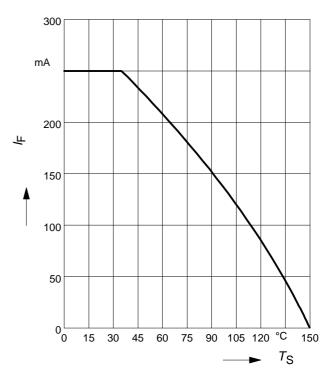


Forward current $I_{\rm F} = f (V_{\rm F})$

 $T_{\rm A} = 25^{\circ}{\rm C}$

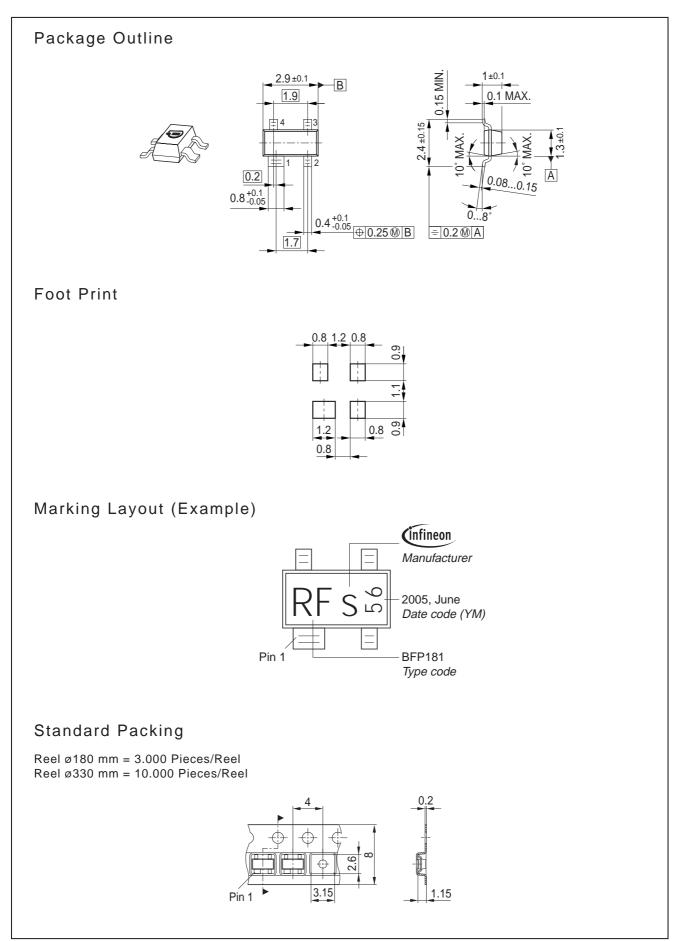


Forward current $I_{\mathsf{F}} = f(T_{\mathsf{S}})$ BAW101



3





4



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